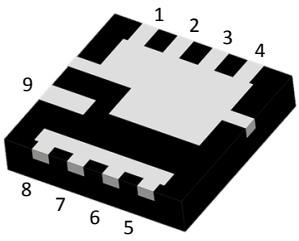
MOSFET

OptiMOS™ 5 Power-Transistor, 25 V

PG-TTFN-9-1



Features

- Very low on-resistance $R_{DS(on)}$
- 100% avalanche tested
- Superior thermal resistance
- N-channel, logic level
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Fully qualified according to JEDEC for Industrial Applications

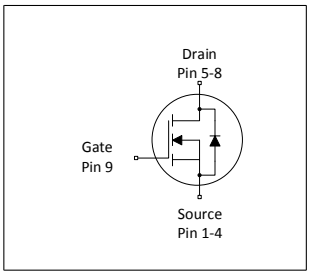


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	25	V
$R_{DS(on),max}$	0.65	mΩ
I_D	298	A
Q_{oss}	41	nC
Q_G(0V..4.5V)	29	nC

Type / Ordering Code	Package	Marking	Related Links
IQE006NE2LM5CG	PG-TTFN-9-1	006E2C5	-

Table of Contents

Description 1
Maximum ratings 3
Thermal characteristics 3
Electrical characteristics 4
Electrical characteristics diagrams 6
Package Outlines 10
Revision History 13
Trademarks 13
Disclaimer 13

1 Maximum ratings

at T_A=25 °C, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current[1]	I_D	- - -	- - -	298 188 41	A	V_{GS}=10 V, T_C=25 °C V_{GS}=10 V, T_C=100 °C V_{GS}=4.5 V, T_A=25 °C, R_{THJA}=60 °C/W[2]
Pulsed drain current[3]	$I_{D,pulse}$	-	-	1192	A	T_A=25 °C
Avalanche energy, single pulse[4]	E_{AS}	-	-	140	mJ	I_D=20 A, R_{GS}=25 Ω
Gate source voltage	V_{GS}	-16	-	16	V	-
Power dissipation	P_{tot}	- -	- -	89 2.1	W	T_C=25 °C T_A=25 °C, R_{THJA}=60 °C/W[2]
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.4	°C/W	-
Device on PCB, 6 cm² cooling area	R_{thJA}	-	-	60	°C/W	-

[1] Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature at 25°C. For higher case temperature please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.
[2] Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.
[3] See Diagram 3 for more detailed information
[4] See Diagram 13 for more detailed information

3 Electrical characteristics

at T_j=25 °C, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	25	-	-	V	V_{GS}=0 V, I_D=1 mA
Gate threshold voltage	$V_{GS(th)}$	1.2	1.6	2	V	V_{DS}=V_{GS}, I_D=250 µA
Zero gate voltage drain current	I_{DSS}	- -	0.1 10	1 100	µA	V_{DS}=20 V, V_{GS}=0 V, T_j=25 °C V_{DS}=20 V, V_{GS}=0 V, T_j=125 °C
Gate-source leakage current	I_{GSS}	-	10	100	nA	V_{GS}=16 V, V_{DS}=0 V
Drain-source on-state resistance	$R_{DS(on)}$	- -	0.50 0.65	0.65 0.80	mΩ	V_{GS}=10 V, I_D=20 A V_{GS}=4.5 V, I_D=20 A
Gate resistance[1)]	R_G	-	0.7	1.2	Ω	-
Transconductance	g_{fs}	-	220	-	S	$\|V_{DS}\|\geq 2\|I_D\|R_{DS(on)max}$, I_D=20 A

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance[1)]	C_{iss}	-	4100	5453	pF	V_{GS}=0 V, V_{DS}=12 V, f=1 MHz
Output capacitance[1)]	C_{oss}	-	1700	2261	pF	V_{GS}=0 V, V_{DS}=12 V, f=1 MHz
Reverse transfer capacitance[1)]	C_{rss}	-	130	195	pF	V_{GS}=0 V, V_{DS}=12 V, f=1 MHz
Turn-on delay time	$t_{d(on)}$	-	5.3	-	ns	V_{DD}=12 V, V_{GS}=4.5 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Rise time	t_r	-	2.6	-	ns	V_{DD}=12 V, V_{GS}=4.5 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Turn-off delay time	$t_{d(off)}$	-	27.0	-	ns	V_{DD}=12 V, V_{GS}=4.5 V, I_D=20 A, $R_{G,ext}$=1.6 Ω
Fall time	t_f	-	5.3	-	ns	V_{DD}=12 V, V_{GS}=4.5 V, I_D=20 A, $R_{G,ext}$=1.6 Ω

Table 6 Gate charge characteristics[2)]

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	9.2	-	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge at threshold	$Q_{g(th)}$	-	5.8	-	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate to drain charge[1)]	Q_{gd}	-	5.6	8.4	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Switching charge	Q_{sw}	-	9.0	-	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	28.5	37.9	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate plateau voltage	$V_{plateau}$	-	2.2	-	V	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 4.5 V
Gate charge total[1)]	Q_g	-	61.7	82.1	nC	V_{DD}=12 V, I_D=20 A, V_{GS}=0 to 10 V
Gate charge total, sync. FET	$Q_{g(sync)}$	-	60.4	-	nC	V_{DS}=0.1 V, V_{GS}=0 to 10 V
Output charge	Q_{oss}	-	41.3	-	nC	V_{DD}=12 V, V_{GS}=0 V

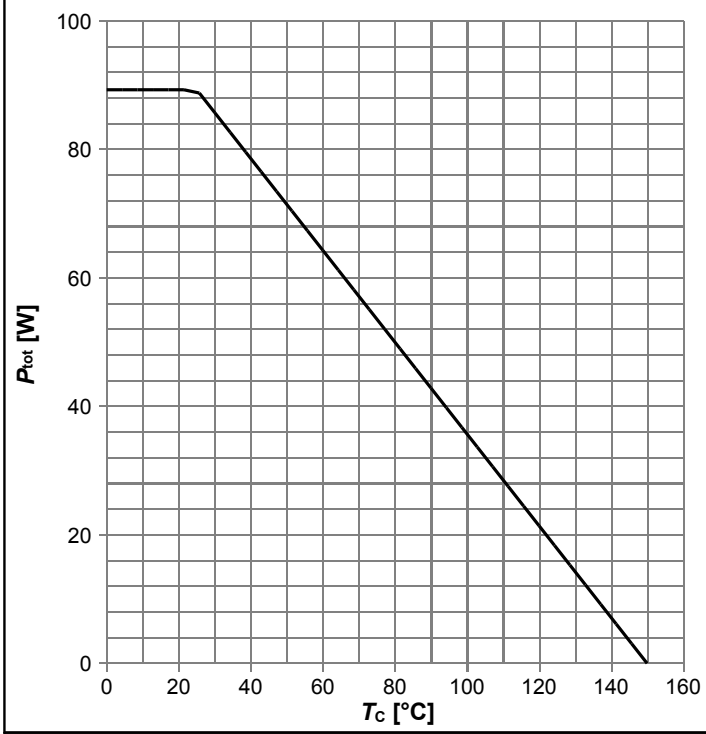
[1)] Defined by design. Not subject to production test.
[2)] See ″Gate charge waveforms″ for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	83	A	T_C=25 °C
Diode pulse current	$I_{S,pulse}$	-	-	1192	A	T_C=25 °C
Diode forward voltage	V_{SD}	-	0.75	1	V	V_{GS}=0 V, I_F=20 A, T_j=25 °C
Reverse recovery charge	Q_{rr}	-	25	-	nC	V_R=12 V, I_F=20 A, di_F/dt=100 A/µs

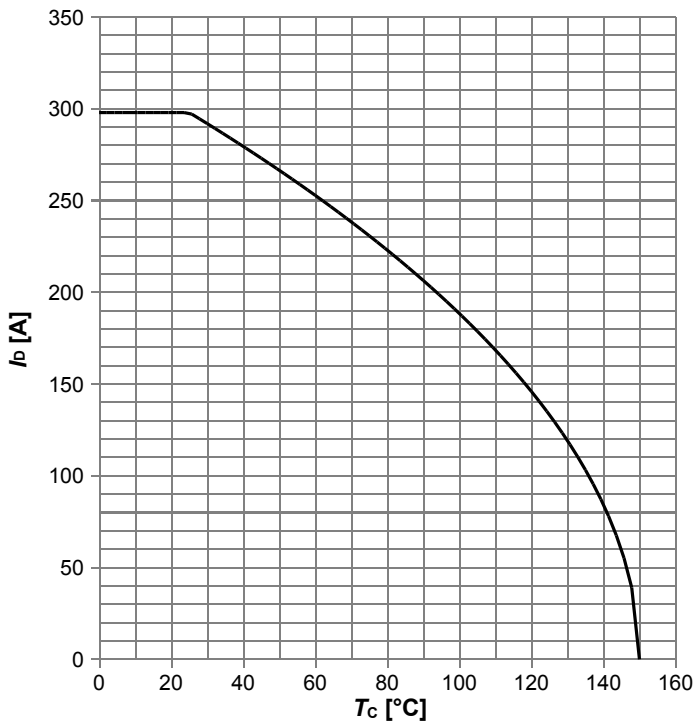
4 Electrical characteristics diagrams

Diagram 1: Power dissipation



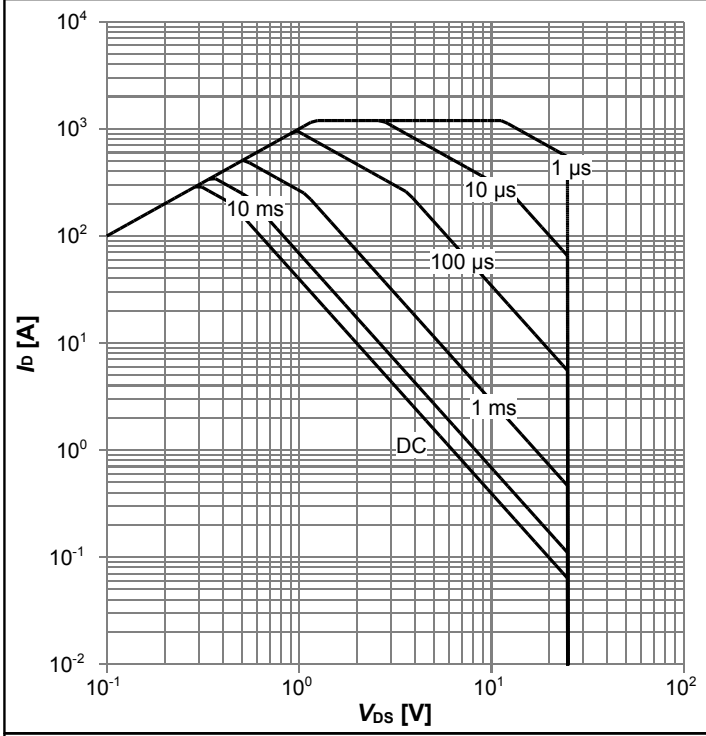
$P_{tot}=f(T_C)$

Diagram 2: Drain current



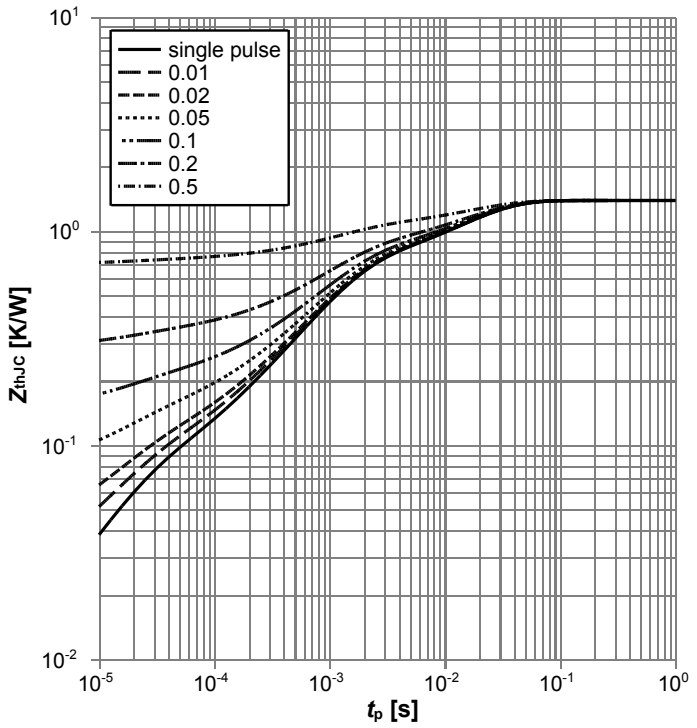
$I_D=f(T_C)$; $V_{GS}\geq 10$ V

Diagram 3: Safe operating area



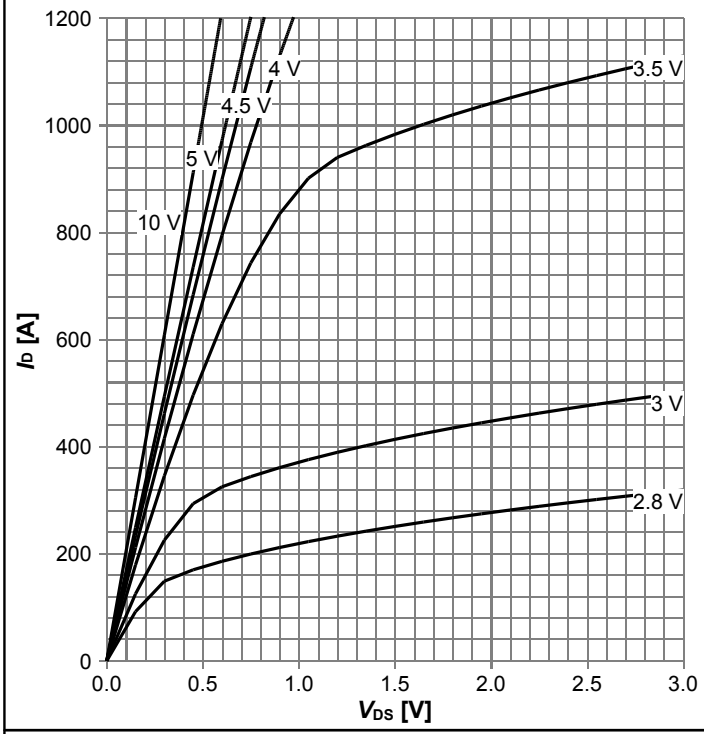
$I_D=f(V_{DS})$; $T_C=25$ °C; $D=0$; parameter: t_p

Diagram 4: Max. transient thermal impedance



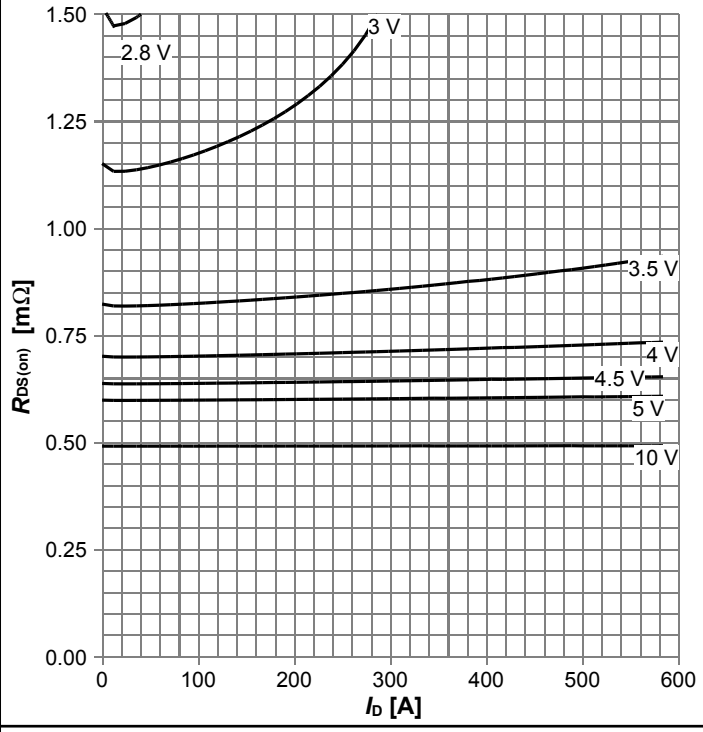
$Z_{thJC}=f(t_p)$; parameter: $D=t_p/T$

Diagram 5: Typ. output characteristics



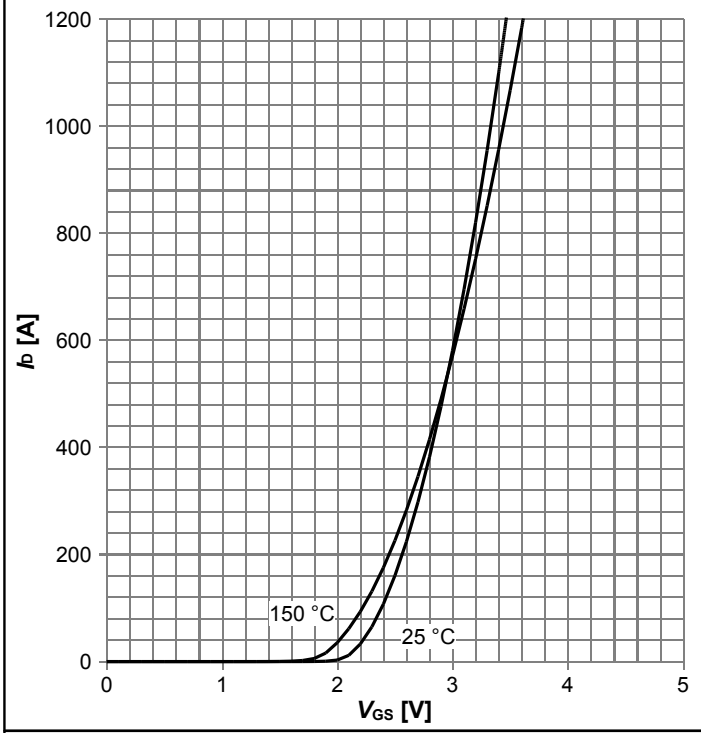
I_D=f(V_{DS}), T_j=25 °C; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



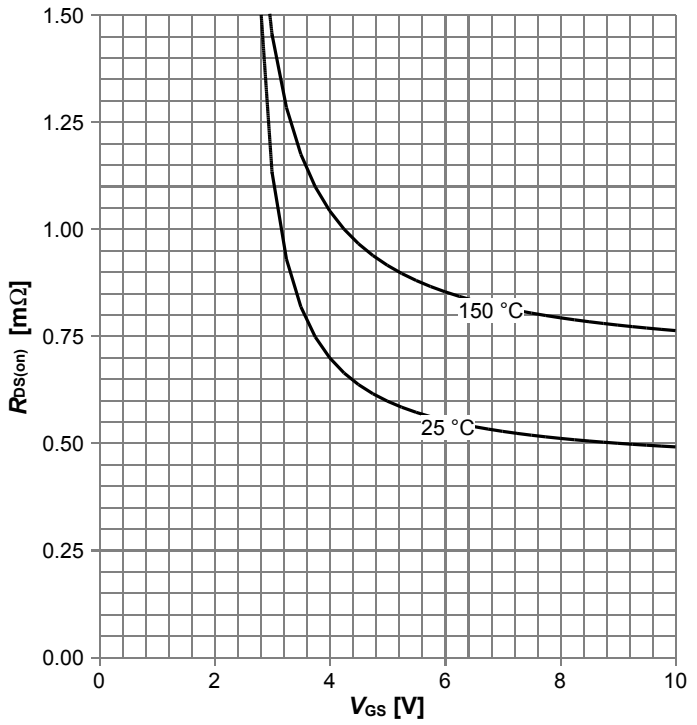
$R_{DS(on)}$=f(I_D), T_j=25 °C; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



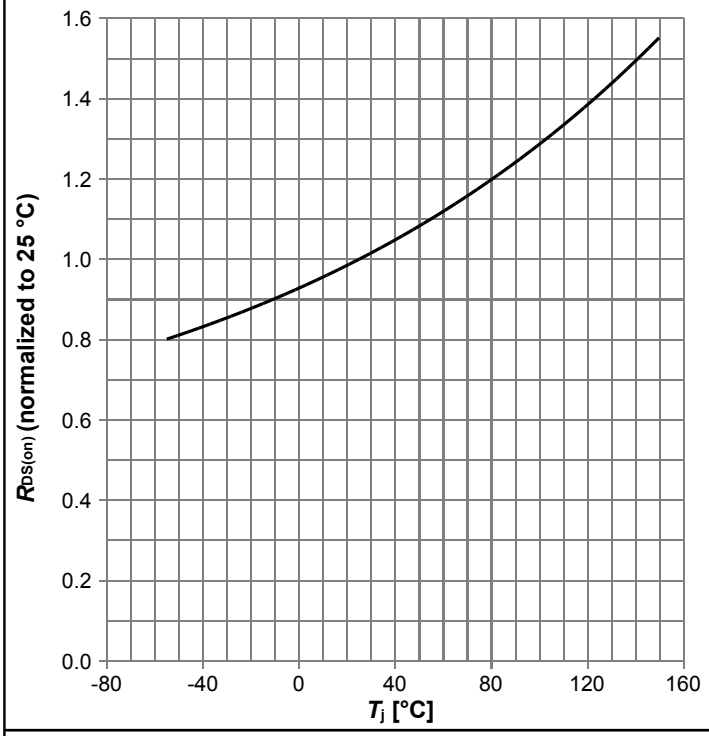
I_D=f(V_{GS}), |V_{DS}|>2|I_D|$R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. drain-source on resistance



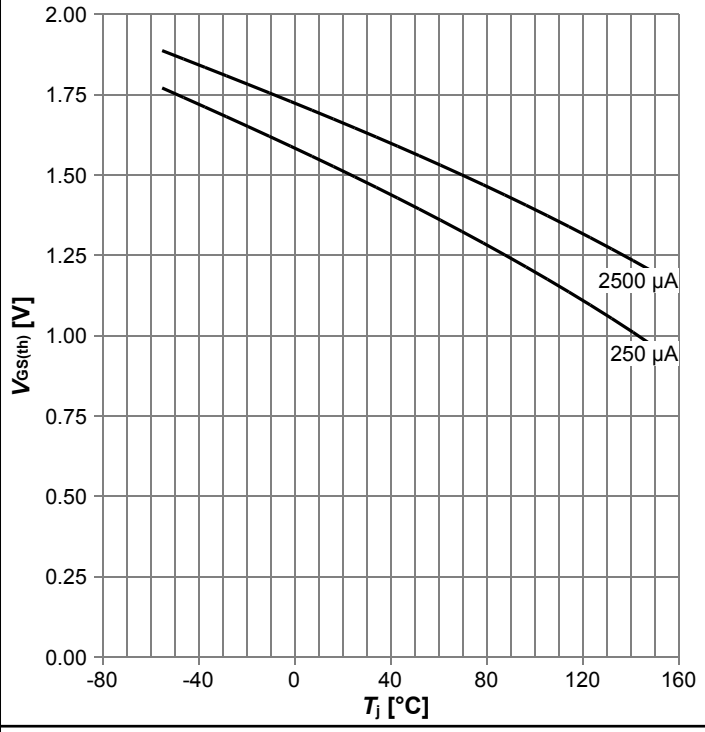
$R_{DS(on)}$=f(V_{GS}), I_D=20 A; parameter: T_j

Diagram 9: Normalized drain-source on resistance



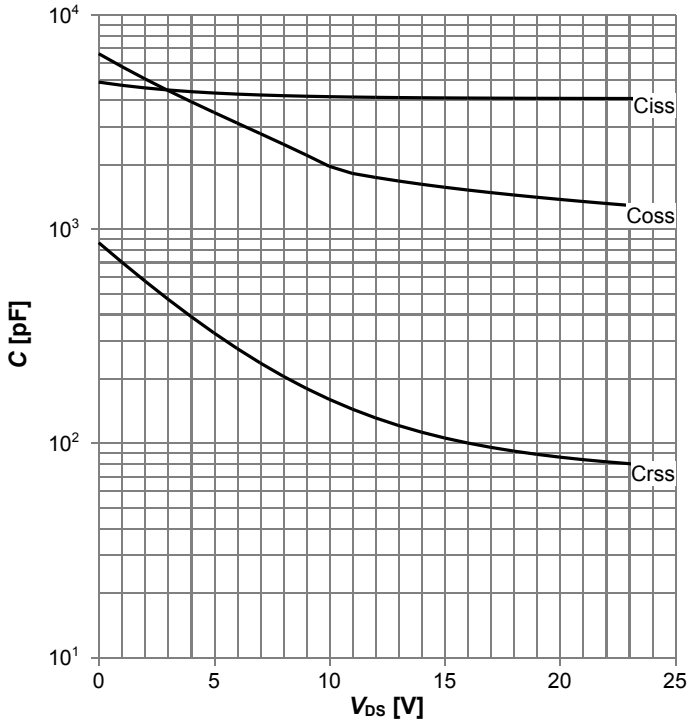
$R_{DS(on)}$=f(T_j), I_D=20 A, V_{GS}=10 V

Diagram 10: Typ. gate threshold voltage



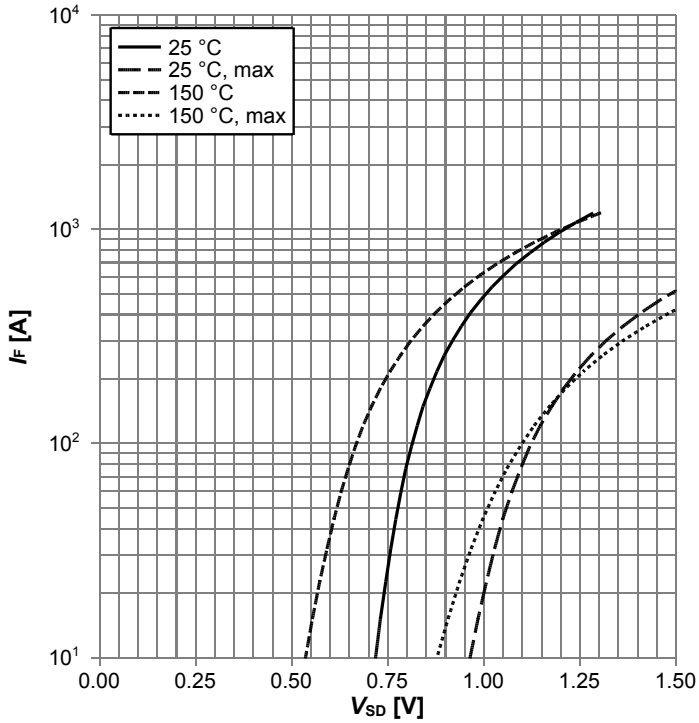
$V_{GS(th}$=f(T_j), V_{GS}=V_{DS}; parameter: I_D

Diagram 11: Typ. capacitances



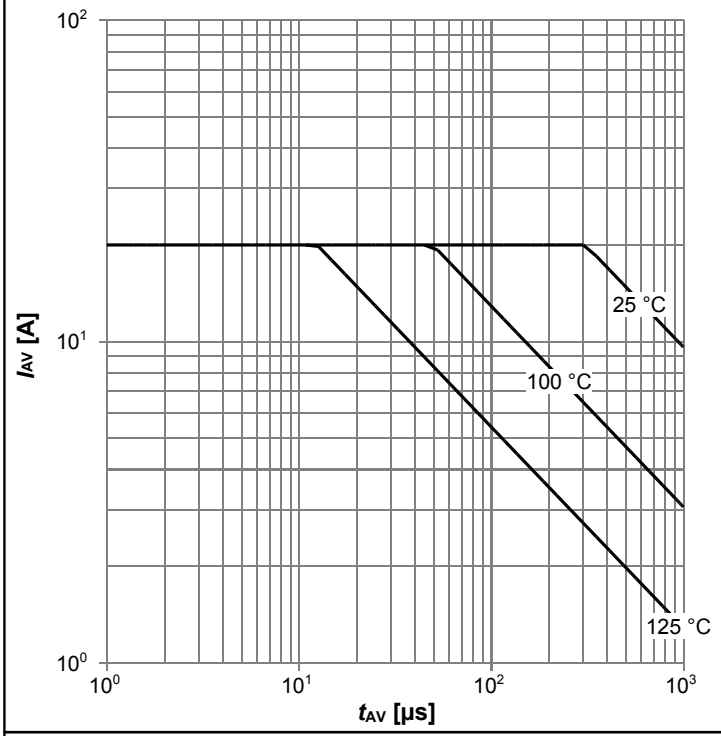
C=f(V_{DS}); V_{GS}=0 V; f=1 MHz

Diagram 12: Forward characteristics of reverse diode



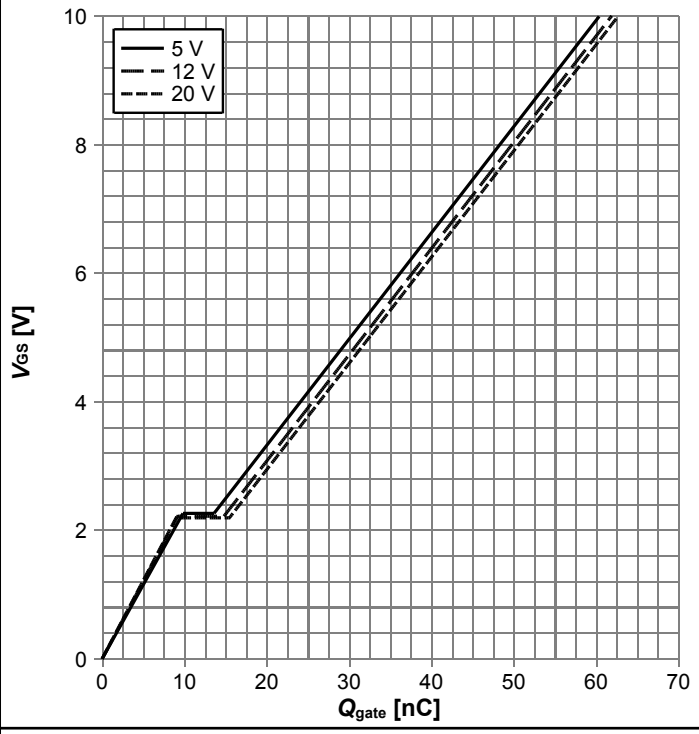
I_F=f(V_{SD}); parameter: T_j

Diagram 13: Avalanche characteristics



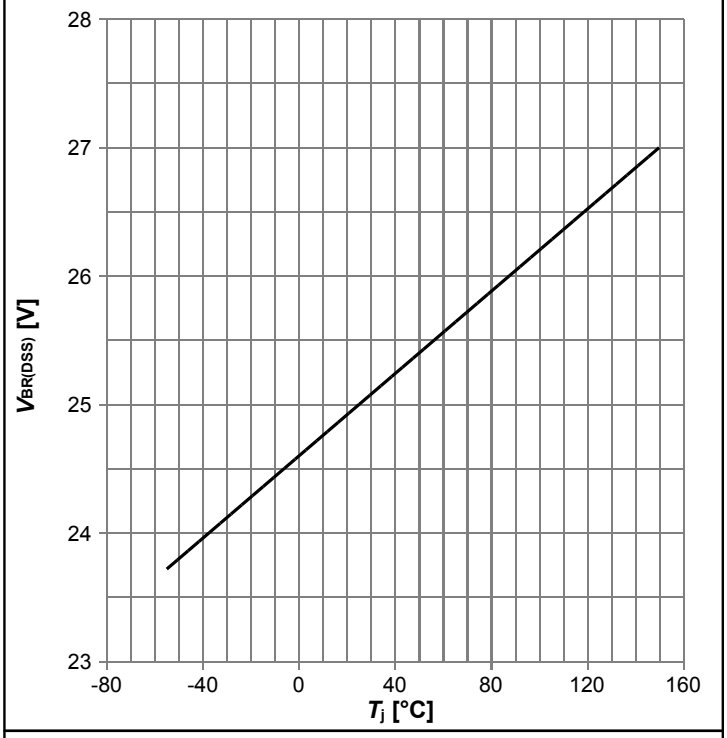
I_{AS}=f(t_{AV}); R_{GS}=25 Ω; parameter: $T_{j,start}$

Diagram 14: Typ. gate charge



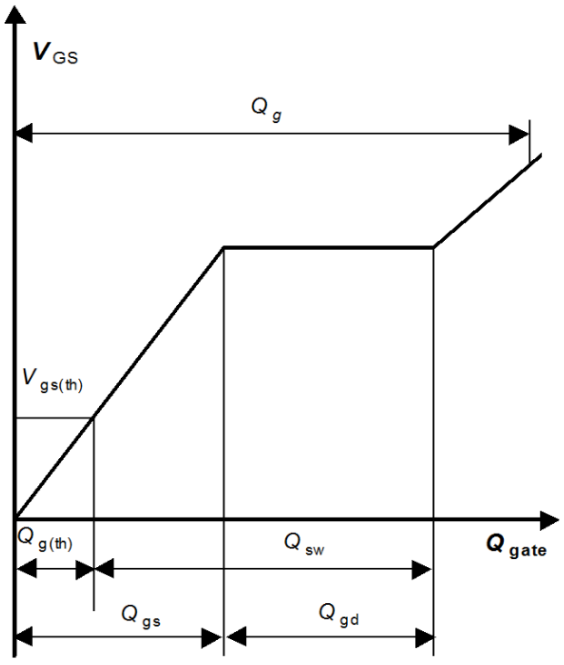
V_{GS}=f(Q_{gate}), I_D=20 A pulsed, T_j=25 °C; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage

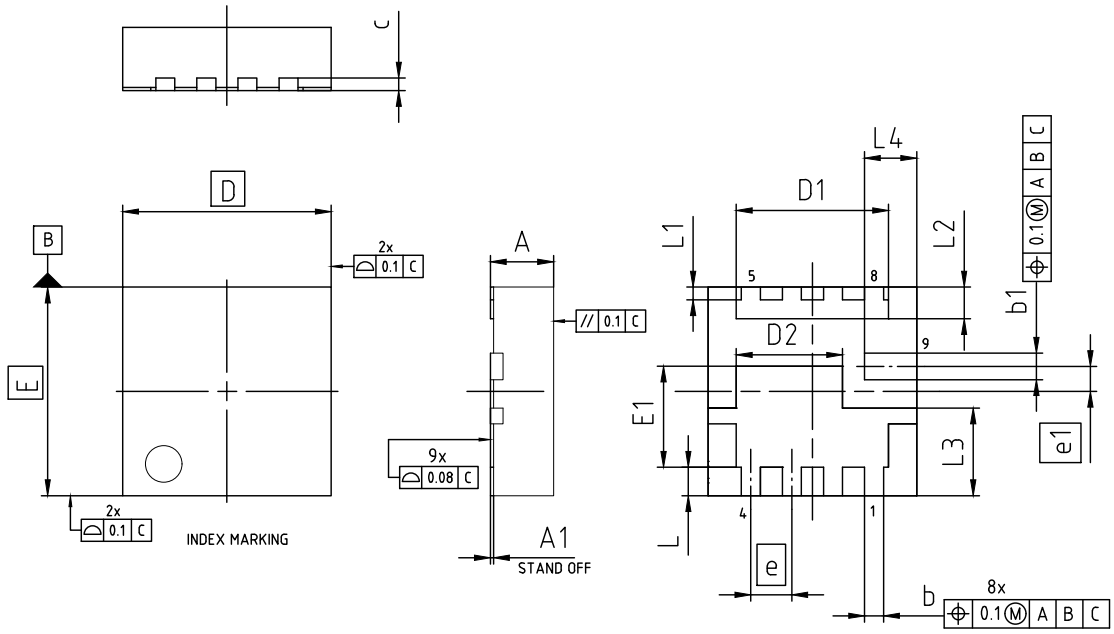


$V_{BR(DSS)}$=f(T_j); I_D=1 mA

Diagram Gate charge waveforms



5 Package Outlines



DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	-	1.10
A1	-	0.05
b	0.20	0.40
b1	0.32	0.52
c	0.20	
D	3.30	
D1	2.31	2.51
D2	1.58	1.78
E	3.30	
E1	1.50	1.70
e	0.65	
e1	0.395	
L	0.35	0.55
L1	0.10	0.30
L2	0.40	0.60
L3	1.285	1.485
L4	0.73	0.93

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REVISION 03
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EUROPEAN PROJECTION
ISSUE DATE 08.11.2019

Figure 1 Outline PG-TTFN-9-1, dimensions in mm

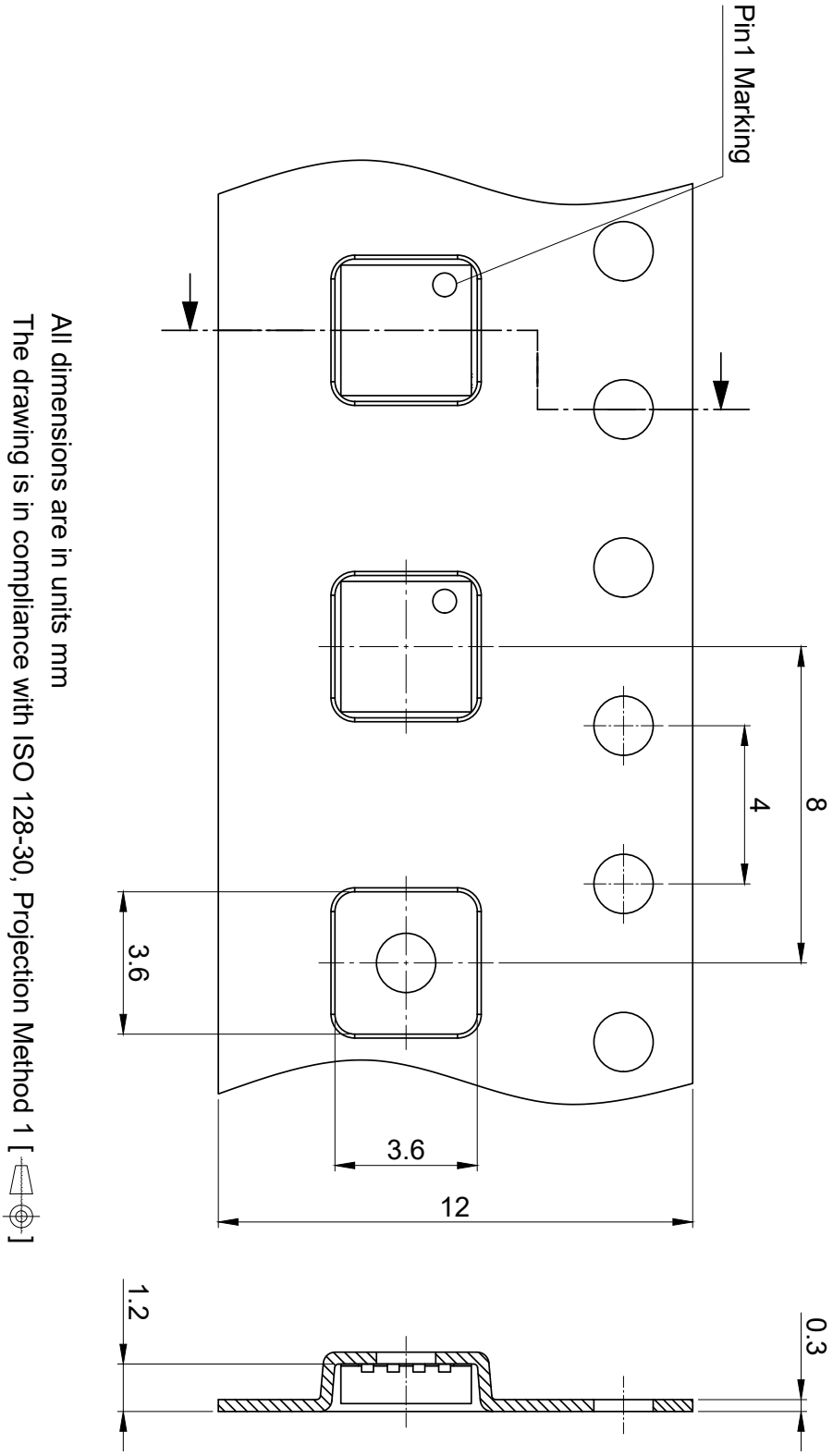


Figure 2 Outline Tape (PG-TTFN-9-1), dimensions in mm

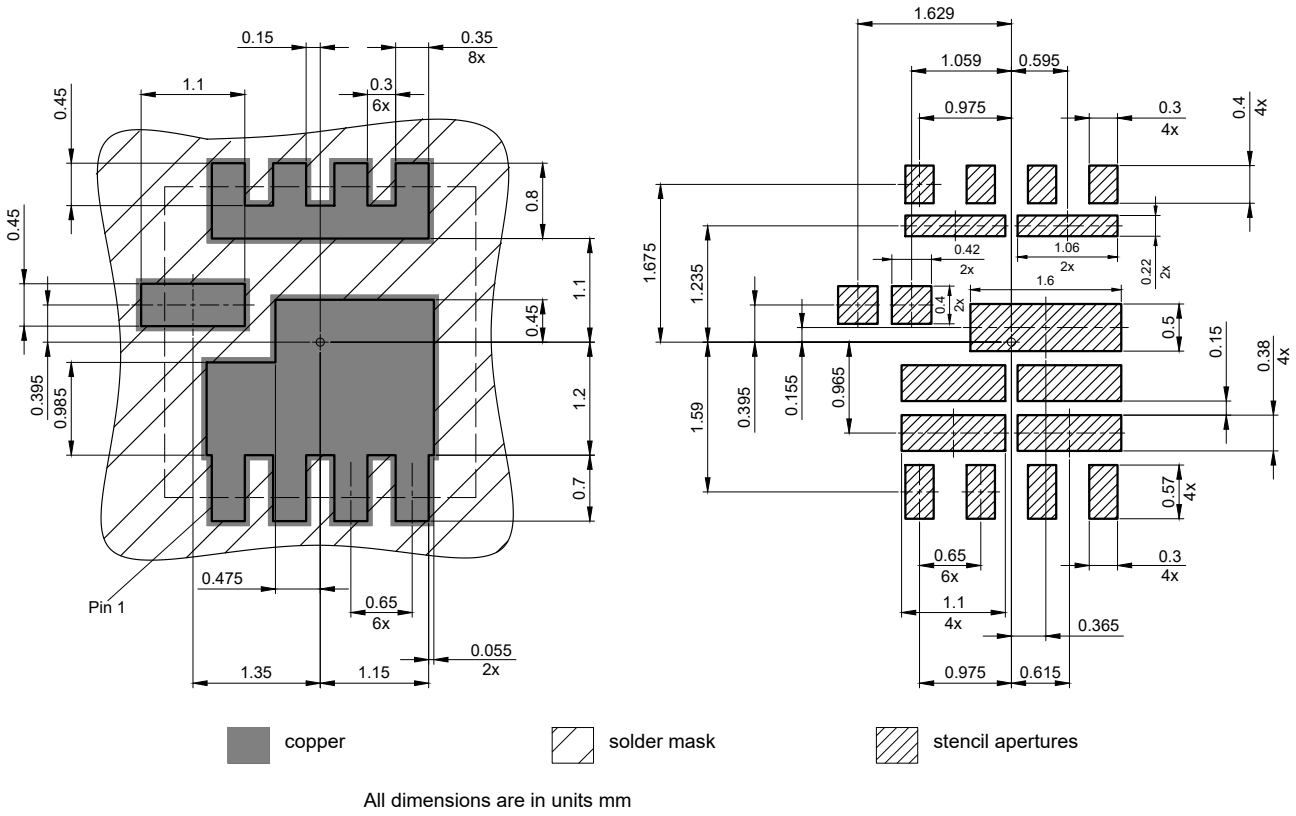


Figure 3 Outline Boardpad (PG-TTFN-9-1), dimensions in mm

Revision History

IQE006NE2LM5CG

Revision: 2020-03-16, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2019-12-06	Release of final version
2.1	2020-03-16	Update footnotes and marking

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